

Dual Ultra-Low Vos Matched Operational Amplifier

OP207

1.0 **SCOPE**

This specification documents the detail requirements for space qualified product manufactured on Analog Devices, Inc.'s QML certified line per MIL-PRF-38535 Level V except as modified herein. The manufacturing flow described in the STANDARD SPACE LEVEL PRODUCTS PROGRAM brochure is to be considered a part of this specification http://www.analog.com/aerospace This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/OP207

2.0 **Part Number**. The complete part number(s) of this specification follow:

Part Number

Description

OP207-903Y

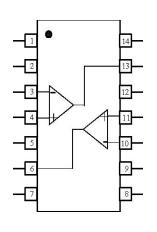
Dual Ultra-Low Vos Matched Operational Amplifier

| <u>Letter</u> | <u>Descriptive designator</u> |
|---------------|-------------------------------|
| Y | GDIP1-T14 |

Case Outline (Lead Finish per MIL-PRF-38535) 14-Lead ceramic dual-in-line package (CERDIP)

NOTES:

- 1. Device may be operated even if insertion is reversed; this is due to inherent symmetry of pin locations of amplifiers A and B
- 2. V-(A) and V-(B) are internally connected via substrate resistance



V+ (A) 14 13 OUT (A) 12 V- (A) 11 +IN (B) 10 -IN (B) 9 NULL (B) 8 NULL (B) 7 V+ (B) 6 OUT (B) 5 V- (B) 4 +IN (A) 3 -IN (A) 2 NULL (A) 1 NULL (A)

Figure 1 - Terminal connections.

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3.0 **Absolute Maximum Ratings**. ($T_A = 25^{\circ}C$, unless otherwise noted)

| Supply Voltage | .±22V |
|---------------------------------------|----------------|
| Power Dissipation | 500mW |
| Differential Input Voltage | ±30V |
| Input Voltage (Note 1) | ±22V |
| Output Short-Circuit Duration | Indefinite |
| Operating Temperature Range | 55°C to +125°C |
| Storage Temperature Range | 65°C to +150°C |
| Lead Temperature (Soldering, 60 sec.) | +300°C |

NOTES:

For supply voltages less than $\pm 22V$, the absolute maximum input voltage is equal to the supply voltages.

3.1 Thermal Characteristics:

Thermal Resistance, CERDIP (Y) Package

Junction-to-Case (Θ JC) = 29°C/W Max

Junction-to-Ambient (Θ JA) = 91°C/W Max

4.0 **Electrical Table**:

| | | Table I | | | | |
|---|----------------------|---|---------------|--------------|--------------|------------|
| Parameter See notes at end of table | Symbol | Conditions Note 1 | Sub- group | Limit Min | Limit Max | Units |
| See notes at end of table | | 1 tote 1 | 1 group | 141111 | 100 | μV |
| Input Offset Voltage | V_{OS} | | 2, 3 | | 230 | μν |
| input officer voltage | 108 | M D L R 3/ | 1 | | 500 | |
| Average Input Offset Voltage Drift 4/ | TCV _{OS} | M, D, L, R <u>3/</u> TA = -55°C, +25°C, +125°C | 1, 2, 3 | | 1.3 | μV/°C |
| | | | 1 | | 2.8 | nA |
| Input Offset Current | I_{OS} | | 2, 3 | | 5.6 | |
| | | M, D, L, R <u>3</u> / | 1 | | 25 | |
| | | | 1 | | ±3.0 | |
| Input Bias Current | I_{B} | | 2, 3 | | ±5.6 | |
| | | M, D, L, R <u>3</u> / | 1 | | ±125 | |
| Input Voltage Range 4/ | IVR | Note 2 | 1, 2, 3 | ±13 | | V |
| Common-Mode Rejection Ratio | C) (D) | $VCM = \pm 13V$ | 1 | 106 | | dB |
| <u>4/</u> | CMRR | TIG ATT 10TT | 2, 3 | 103 | 20 | |
| Power Supply Rejection Ratio | PSRR | $VS = \pm 3V$ to $\pm 18V$ | 1 | | 20 | $\mu V/V$ |
| <u>4</u> / | | D. 40110 | 2, 3 | . 10. 5 | 32 | * 7 |
| | *** | $RL = 10K\Omega$ | 4 | ±12.5 | | V |
| Output Voltage Swing 4/ | V_{O} | $RL = 2K\Omega$ | 4, 5, 6 | ±12 | | |
| | | $RL = 1K\Omega$ | 4 | ±10 | | / |
| | | $VO = \pm 10V$, $RL = 2K\Omega$ | 4 | 200 | | V/mV |
| Large Signal Voltage Gain | A_{VO} | | 5, 6 | 150 | | |
| | | M, D, L, R <u>3</u> / | 4 | 100 | 0 | |
| Power Supply Current | I_{SY} | No Load, Both Amplifiers M, D, L, R 3/ | 1 1 | | 8 | mA |
| Input Noise Voltage 4/ | e _n | $f_0 = 1$ Hz to 100 Hz | 7 | | 150 | nV_{RMS} |
| Input Noise Current 4/ | i _n | $f_0 = 1$ Hz to 100 Hz | 7 | | 8 | pA_{RMS} |
| | V _{OS} adj+ | $Rp = 20K\Omega$ | 1 | 0.5 | | mV |
| Offset Adjustment Range 4/ | V _{OS} adj- | $Rp = 20K\Omega$ | 1 | | -0.5 | |
| I + 0.00 + 37.14 - 34.41 - 4/ | | | 1 | | 90 | μV |
| Input Offset Voltage Match 4/ | ΔVOS | | 2, 3 | | 180 | • |
| Average Non- Inverting Bias | AID : | | 1 | | ±3.5 | nA |
| Current <u>4</u> / | ΔIB+ | | 2, 3 | | ±6.0 | |
| Non Inverting Offset Current 4/ | AIOC I | | 1 | | ±3.5 | |
| Non-Inverting Offset Current <u>4</u> / | ΔIOS+ | | 2, 3 | | ±6.5 | |
| Inverting Offset Current 4/ | ΔIOS- | | 1 | | ±3.5 | |
| _ | | | 2, 3 | 102 | ±6.5 | מג |
| Common Mode Rejection Ratio Match <u>4/</u> | ΔCMRR | | 2, 3 | 103 100 | | dB |
| Power Supply Rejection Ratio | ADCDD | $V_S = \pm 3V$ to $\pm 18V$ | 1 | | 32 | μV/V |
| Match $\frac{4}{}$ | ΔPSRR | | 2, 3 | | 51 | • |
| | I _{SC} + | | 1 | 5 | 58 | mA |
| Output Short Circuit Current <u>4</u> / | I _{SC} - | | 1 | -55 | -5 | |
| Channel Separation <u>4</u> / | CS | | 4 | 126 | | dB |

TABLE I NOTES:

- $1/V_S = \pm 15V$, $R_S = 50$ ohm, unless otherwise specified
- $2/I_{VR}$ is defined as the V_{CM} range used for the CMRR test.
- 3/ Post irradiation limit. Subgroup 1 parameters without limit are read and recorded but not guaranteed.
- 4/ Not tested post irradiation.

4.1 Electrical Test Requirements:

| Table II | |
|---|---|
| Test Requirements | Subgroups (in accordance with MIL-PRF-38535, Table III) |
| Interim Electrical Parameters | 1 |
| Final Electrical Parameters | 1, 2, 3, 4, 5, 6, 7 <u>1/2/</u> |
| Group A Test Requirements | 1, 2, 3, 4, 5, 6 |
| Group C end-point electrical parameters | 1 <u>2/</u> |
| Group D end-point electrical parameters | 1 |
| Group E end-point electrical parameters | 1 |

Notes:

1/ PDA applies to subgroup 1. VOS and delta's excluded from PDA.

2/ See table III for delta limits.

4.2 Table III. Burn-in test delta limits.

| | | Table III | | |
|----------------------|----------|-----------|-------|-------|
| TEST | BURN-IN | LIFETEST | DELTA | |
| TITLE | ENDPOINT | ENDPOINT | LIMIT | UNITS |
| V_{OS} | ±100 | ±175 | ±75 | μV |
| $\pm I_{\mathrm{B}}$ | ±3 | ±4 | ±1 | nA |

5.0 Life Test/Burn-In Circuit:

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B (see figure 2).
- 5.3 Steady state life test is per MIL-STD-883 Method 1005, test condition B.

| Rev | Description of Change | Date |
|-----|---|---------------|
| A | Initiate | Mar. 28, 2000 |
| В | Update web address. Correct PSRR units from V/µV to µV/V. Table | Mar. 19, 2002 |
| | I: reference to note 4 deleted, note 4 not in datasheet. Symbol for | |
| | Inverting offset current should be Δ IOS Table II, note 1 add | |
| | "VOS and delta's excluded from PDA". Update Table III with Life | |
| | test end-point = datasheet + delta. | |
| С | Update web address. Add note 4 to indicate parameters not tested post irradiation | May 13, 2003 |
| D | Delete burn-in and radiation bias circuits | Aug. 5, 2003 |
| Е | Updated header/footer & added to scope description, and deleted OP207R903Y – part is no longer offered. | Feb. 14, 2008 |
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